



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Doak et al. : Group Art Unit: 2822
Serial No.: 09/887,777 : Examiner: Parviz Hassanzadeh
Filed: June 22, 2001 :
Title: **Method and Apparatus for Preparing Nitride Semiconductor Surfaces**

RESPONSE TO OFFICIAL ACTION

Box Non-Fee Amendment
Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

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FEB 27 2003
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FEB 24 2003
TECHNOLOGY CENTER 2822

In response to the Official Action mailed September 25, 2002, please amend and reconsider the above-identified application as shown below and in view of the remarks that follow.

In the Specification

Substitute enclosed new pages 6 and 7 for those presently in the application.

In the Claims

Cancel nonelected claims 2 - 11 and 19 - 35, without prejudice.

Kindly substitute the following rewritten claims 12 - 15 and 36 for those currently appearing in the application and kindly add the following new claims 39 - 52.

12. (Amended) An apparatus for producing nitride films comprising:
- (a) a pair of corona-discharge producing electrodes,
 - (b) a nitrogen delivery path leading to a nozzle at which the electrodes produce a corona discharge, and
 - (c) means to locate a substrate along the nitrogen delivery path downstream of the location at which the electrodes produce the corona discharge for deposition thereon of nitrogen activated by the corona discharge at a location sufficiently distant from the corona-